

Extrinsic Semiconductors

Recap :

n_i = Intrinsic charge-carrier density.

$$n_i(E, T)$$

In Silicon; $n_i(E_g = 1.1 \text{ eV}; T = 0 \text{ K}) = 0 \text{ cm}^{-3}$

$$n_i(E_g = 1.1 \text{ eV}; T = 300 \text{ K}) = 10^{10} \text{ cm}^{-3}$$

25 meV of thermal energy

Si-atom

$$\frac{22}{10} \text{ cm}^{-3}$$

Since, $n = p = n_i$

$$np = n_i^2$$

n = electrons cm^{-3}
 p = holes cm^{-3}

What is extrinsic mean which controls the carrier-density?

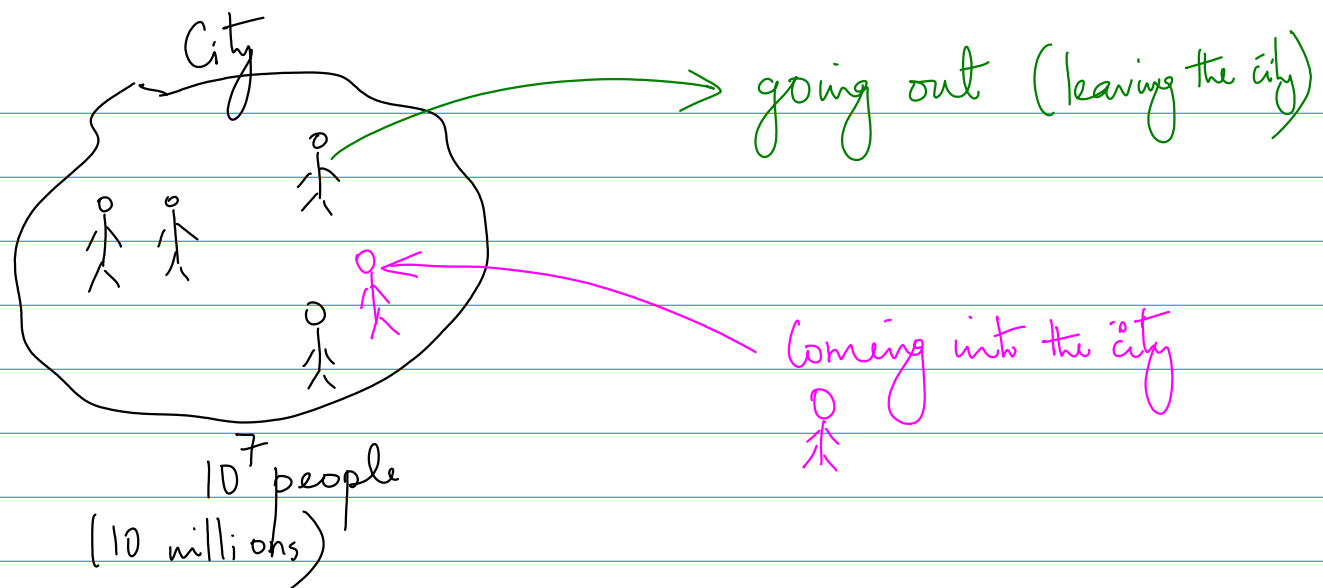
$$\sigma_e = e \mu n$$

electronic density (cm^{-3})

electronic charge mobility

if we control the electronic density (n) by some extrinsic mean, we can control the conductivity.

Extrinsic Mean — Doping.

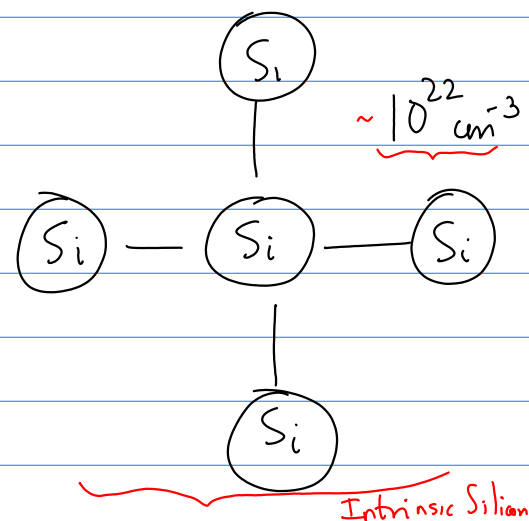


Out of 10 million population, if one is replaced with other, then, effectively there is no-change in the distribution of the people in the city.

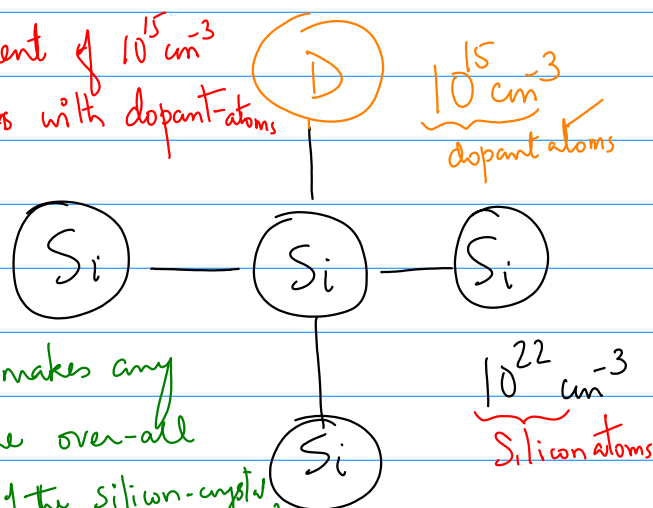
Doping of Silicon:

Silicon atom density: 10^{22} cm^{-3}

Dopant density: 10^{15} cm^{-3}



Replacement of 10^{15} cm^{-3} Silicon atoms with dopant-atoms



Ques: Will this process of doping makes any change in the over-all properties of the silicon-crystal?

Out of 10^{22} Silicon atoms only one Silicon atom is replaced with the Dopant-atom.

As a result, one cannot see any change in the mechanical properties of the Silicon.

However, the electronic properties changes. How?

Lets see dopant is a "donor". (Which can donate electron)

$$\text{Si atomic density} = 5 \times 10^{22} \text{ cm}^{-3}$$

$$\text{Donor density} = 1 \times 10^{15} \text{ cm}^{-3}$$

\Rightarrow Out of 5×10^{22} Silicon atoms cm^{-3} , 1 Silicon atom is being replaced with the donor-atom.

\Rightarrow The donor is 20 parts per billion (ppb)

Si atoms
of 1 billion
population

\rightarrow 20 atoms are the extrinsic one (donor-atom)

Our focus is the electronic effect:

$$\sigma = e \mu n$$

Intrinsic Conductivity $\sigma_i = e \mu n_i$

Extrinsic Conductivity
(due to doping)

$$\sigma_{ex} = e \mu n_D$$

$$\left\{ n = p = n_i = 10^{10} \text{ cm}^{-3} \right\}$$

$$n_D = \text{Dopant density cm}^{-3} = 10^{15} \text{ cm}^{-3}$$

Ratio of conductivities $= \frac{\sigma_{ex}}{\sigma_i} = \frac{\cancel{\mu} N_D}{\cancel{\mu} N_i} = \frac{10^{15} \text{ cm}^{-3}}{10^{10} \text{ cm}^{-3}} = \underline{10^5}$

$$\sigma_{ex} = 10^5 \sigma_i$$

\Rightarrow Conductivity of the Silicon enhances by five Order of magnitude.

Analogy: Wallet is having Rs. 100.

if it is enhanced with five order of magnitude

$$\text{Rs } 100 \cdot 10^5 = \text{Rs } 10^7 = \text{Rs } 10 \text{ million.} \\ = \text{Rs } 1 \text{ Crore}$$

Two kinds of dopants:

- 1) Donors: Releasing electrons \equiv n-type semiconductors
- 2) Acceptors: Accepting electrons (Releasing holes) \equiv p-type semiconductors

Donors \rightarrow Pentavalent elements P, As, Sb (Antimony) -----

Acceptors - Trivalent elements B, Al, Ga, In ...

\Rightarrow What would be the distribution of "FREE" charge carriers in CB & VB.?